

LISTING OF THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently amended) A process for producing copy protection for an electronic circuit, comprising the steps of:
providing a substrate having semiconductor structures on at least a first side of the substrate;
providing a material for coating the substrate; and
coating the substrate with a copy-protect layer by evaporation coating, wherein the copy-protect layer comprises an at least binary system of glass, and wherein the at least binary system of glass is a material that represents a synthesis of at least two chemical compounds.
2. (Previously presented) The process as claimed in claim 1, wherein the semiconductor structures, at least in regions, are covered by the copy-protect layer, the copy-protect layer being matched to the substrate so that an etching process that dissolves the copy-protect layer likewise attacks the substrate so that the semiconductor structures are at least partially destroyed.
3. (Previously presented) The process as claimed in claim 2, wherein the substrate comprises a semiconductor layer of silicon and the copy-protect layer comprises silicon.
4. (Previously presented) The process as claimed in claim 1, wherein the copy-protect layer is a continuous layer.
5. (Cancelled).
6. (Previously presented) The process as claimed in claim 1, wherein the copy-protect layer comprises a borosilicate glass with aluminum oxide and alkali metal

oxide fractions.

7. (Cancelled).
8. (Previously presented) The process as claimed in claim 1, wherein the copy-protect layer comprises a shield against electromagnetic waves.
9. (Previously presented) The process as claimed in claim 1, wherein coating the substrate with the copy-protect layer comprises evaporation coating induced by thermal evaporation or by electron beam evaporation.
10. (Previously presented) The process as claimed in claim 1, wherein the copy-protect layer is applied to the substrate in a thickness of from 0.01 to 1000 μm .
11. (Previously presented) The process as claimed in claim 1, wherein coating the substrate with the copy-protect layer comprises coating at a bias temperature of below 300°C.
12. (Currently amended) The process as claimed in claim 1, wherein coating the substrate with the copy-protect layer comprises coating at a pressure of from 10^{-3} mbar to 10^{-7} mbar.
13. (Previously presented) The process as claimed in claim 1, further comprising applying a glass layer to a second side of the substrate, wherein the second side is on the opposite side from the first side.
14. (Previously presented) The process as claimed in claim 1, further comprising applying a plastics layer to a second side of the substrate, wherein the second side is on the opposite side from the first side.

15. (Previously presented) The process as claimed in claim 1, further comprising:

- thinning the substrate;
- producing etching pits with connection structure regions on the first side of the substrate;
- applying a plastics layer to a second side of the substrate, wherein the second side is on the opposite side from the first side, the plastics layer being applied so that the connection structure regions remain open;
- producing contacts on the second side by coating with a conductive layer;
- applying a ball grid array; and
- dicing the substrate into individual chips.

16. (Previously presented) The process as claimed in claim 15, further comprising removing the plastics layer from the second side.

17. (Previously presented) The process as claimed in claim 1, further comprising:

- evaporation coating a second side of the substrate with a glass layer that is from 0.01 μm to 50 μm thick; and
- uncovering connection structure regions located beneath the glass layer by grinding or etching.

18. (Previously presented) The process as claimed in claim 15, further comprising filling the etching pits with conductive material.

19. (Previously presented) The process as claimed in claim 1, further comprising:

coating the connection structures with a structured covering layer before the coating with the copy-protect layer;

thinning the copy-protect layer at least until the structured covering layer has been uncovered; and

removing the structured covering layer to uncover the connection structure regions.

20. (Previously presented) The process as claimed in claim 19, wherein at least sections of the structured covering layer and at least sections of the copy-protect layer are removed by a lift-off technique.

21. (Previously presented) The process as claimed in claim 15, further comprising applying a ball grid array to the first side of the substrate on the connection structure regions.

22. (Previously presented) The process as claimed in claim 1, wherein the semiconductor structures comprise electronic decryption devices.

23. (Cancelled)

24. (Currently amended) The electronic component with copy protection, comprising:

an electronic circuit on a substrate having a first side;

semiconductor structures on the first side; and

a copy-protect layer fixedly joined to at least a region of the semiconductor structures, wherein the copy-protect layer comprises an at least binary system of glass, and wherein the at least binary system of glass is a material that represents a synthesis of at least two chemical compounds.

25. (Previously presented) The electronic component as claimed in claim 24, wherein the copy-protect layer comprises a first material, the first material being selected so that an etching process that dissolves the copy-protect layer destroys a portion of the electronic circuit.

26. (Previously presented) The electronic component as claimed in claim 25, wherein the substrate comprises a semiconductor layer of silicon and the copy-protect layer comprises silicon.

27. (Previously presented) The electronic component as claimed in claim 24, wherein the copy-protect layer is a continuous layer.

28. (Cancelled).

29. (Previously presented) The electronic component as claimed in claim 24, wherein the copy-protect layer comprises a borosilicate glass with aluminum oxide and alkali metal oxide fractions.

30. (Previously presented) The electronic component as claimed in claim 24, wherein the copy-protect layer is an evaporation coating.

31. (Cancelled).

32. (Previously presented) The electronic component as claimed in claim 24, wherein the copy-protect layer shields electromagnetic waves.

33. (Previously presented) The electronic component as claimed in one of claims claim 24, wherein the copy-protect layer is a thermal evaporation coating or an electron-beam evaporation coating.

34. (Previously presented) The electronic component as claimed in claim 24, wherein the copy-protect layer is from 0.01 μm to 1000 μm thick.

35. (Previously presented) The electronic component as claimed in claim 24, further comprising connection structures and elevated connection structures arranged on a second side of the substrate, the second side being on the opposite side from the first side, wherein the elevated connection structures are electrically connected to the connection structures.

36. (Previously presented) The electronic component as claimed in claim 35, wherein the second side is coated with plastic between the elevated connection structures so that the elevated connection structures remain uncovered.

37. (Previously presented) The electronic component as claimed in claim 35, wherein the second side is coated with glass between the elevated connection structures so that the elevated connection structures remain uncovered.

38. (Previously presented) The electronic component as claimed in claim 24, further comprising connection structures and elevated connection contacts arranged on the first side of the substrate, the elevated connection contacts being electrically connected to the connection structures.

39. (Previously presented) The electronic component as claimed in claim 38, wherein the copy-protect layer on the first side of the substrate extends between the elevated connection contacts and the connection structures so that the elevated connection contacts and the connection structures remain uncovered.

40. (Previously presented) The electronic component as claimed in claim 24, further comprising a decryption device.

41. (Previously presented) The electronic component as claimed in claim 24, wherein the copy-protect layer has a first portion and a second portion that have different etching rates.

42. (Previously presented) A decryption device for decrypting encrypted signals, comprising:

- an electronic circuit on a substrate having a first side;
- semiconductor structures on the first side;
- a copy-protect layer fixedly joined to at least a region of the semiconductor structures; and
- a decryption device.

43-45. (Cancelled).